

# 1SS88

## Silicon Schottky Barrier Diode for CATV Balanced Mixer

# HITACHI

Preliminary  
Rev. 0  
Oct 1993

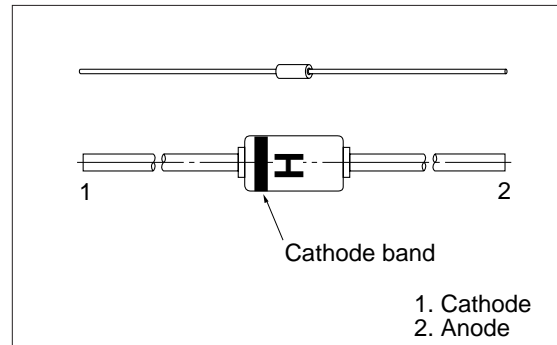
### Features

- Low capacitance. ( $C=0.97\text{pF}$  max)
- High reliability with glass seal.

### Ordering Information

Type No.	Cathode band	Mark	Package Code
1SS88	White	H	DO-35

### Outline



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

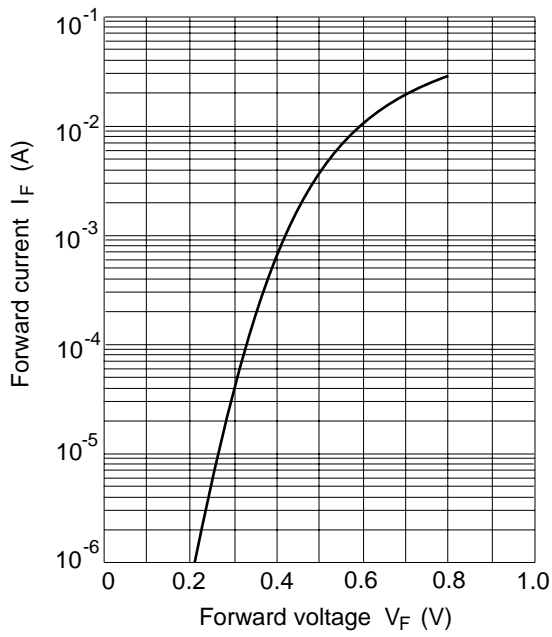
Item	Symbol	Value	Unit
Reverse voltage	$V_R$	10	V
Peak forward current	$I_{FM}$	35	mA
Average forward current	$I_o$	15	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	100	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +100	$^\circ\text{C}$

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

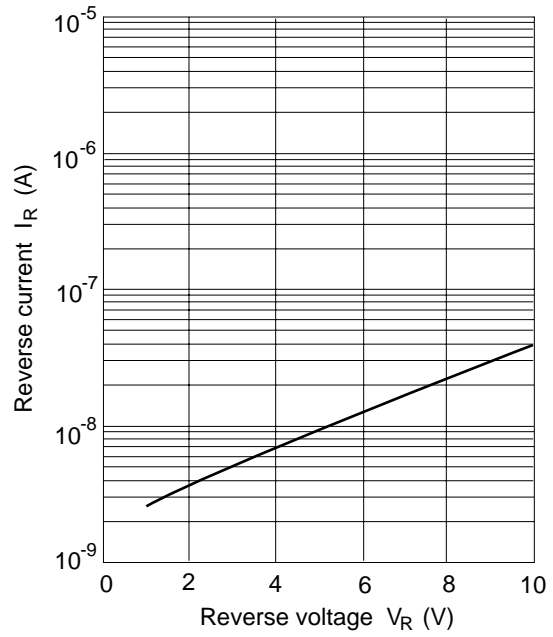
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_{F1}$	365	—	430	mV	$I_F = 1\text{ mA}$
	$V_{F2}$	520	—	600	mV	$I_F = 10\text{ mA}$
Reverse current	$I_{R1}$	—	—	0.2	$\mu\text{A}$	$V_R = 2\text{ V}$
	$I_{R2}$	—	—	10	$\mu\text{A}$	$V_R = 10\text{ V}$
Capacitance	$C$	—	—	0.97	pF	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$
Capacitance deviation	$\Delta C$	—	—	0.1	pF	$V_R = 0\text{ V}$ , $f = 1\text{ MHz}$
Forward voltage deviation	$\Delta V_{F1}$	—	—	10	mV	$I_F = 2.5\text{ mA}$
	$\Delta V_{F2}$	—	—	10	mV	$I_F = 10\text{ mA}$
ESD-Capability	—	30	—	—	V	* $C=200\text{pF}$ , Both forward and reverse direction 1 pulse.

\* Failure criterion ;  $I_R \geq 50\mu\text{A}$  at  $V_R = 10\text{V}$

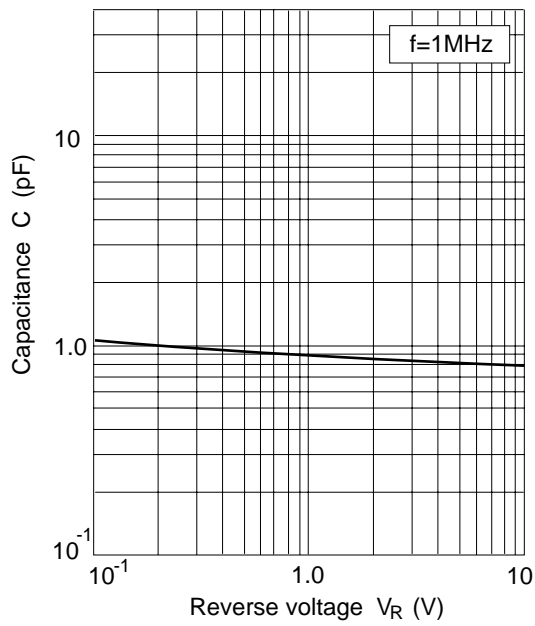
\*\* Each group shall unify a multiple of 4 diodes



**Fig.1 Forward current Vs. Forward voltage**



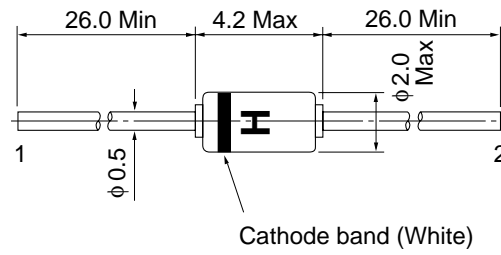
**Fig.2 Reverse current Vs. Reverse voltage**



**Fig.3 Capacitance Vs. Reverse voltage**

## Package Dimensions

Unit: mm



HITACHI Code	DO-35
JEDEC Code	DO-35
EIAJ Code	SC-48
Weight (g)	0.13